

**30 V, dual N-channel Trench MOSFET** 19 April 2016

**Product data sheet** 

### 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a small and leadless DFN2020D-6 (SOT1118D) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

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- Trench MOSFET technology
- Low threshold voltage
- Leadless medium power SMD plastic package: 2 × 2 × 0.65 mm
- Tin-plated 100 % solderable side pads for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

### 3. Applications

- LED driver
- Power management
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
V <sub>GS</sub>	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	3.1	А
Static characteristics (per transistor)							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 3.1 A; T <sub>j</sub> = 25 °C		-	55	72	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	6 5 4	D1 D2
2	G1	gate TR1		
3	D2	drain TR2	7 8	$G1 \xrightarrow{f} G2$
4	S2	source TR2		
5	G2	gate TR2	1 2 3	
6	D1	drain TR1	Transparent top view DFN2020D-6 (SOT1118D)	S1 S2 017aaa256
7	D1	drain TR1	DI 142020D-0 (SOTTIOD)	
8	D2	drain TR2		

# 6. Ordering information

Table 3. Ordering inf	formation		
Type number	Package		
	Name	Description	Version
PMDPB56XNEA	DFN2020D-6	DFN2020D-6: plastic, thermally enhanced ultra thin and small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm	SOT1118D

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
PMDPB56XNEA	3A

### 8. Limiting values

#### Table 5.Limiting values

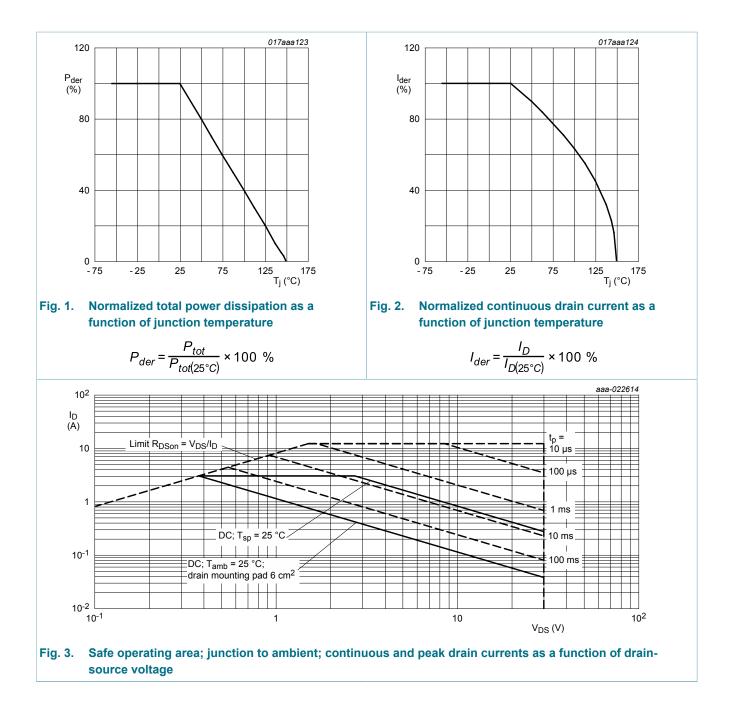
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	3.1	А
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	2	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	12	Α
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 0.3 A; $T_{j(init)}$ = 25 °C; DUT in avalanche (unclamped)		-	6.2	mJ
P <sub>tot</sub> total power dissipa	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	485	mW
			[1]	-	1.15	W
		T <sub>sp</sub> = 25 °C		-	8.33	W
Per device						
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode	,				
ls	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.1	А
ESD Maxim	num rating	·				
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

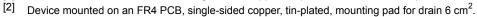
[3] Measured between all pins.

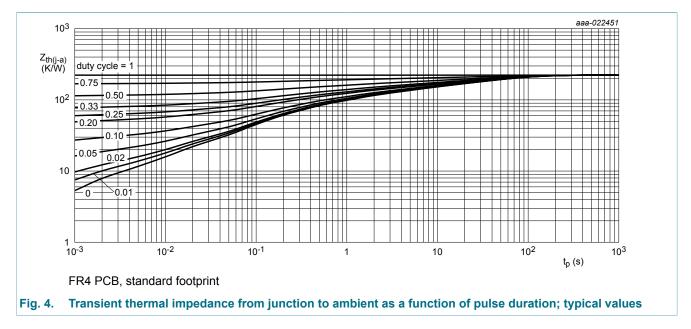


### 9. Thermal characteristics

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	224	257	K/W
	from junction to ambient		[2]	-	96	109	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	12	15	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

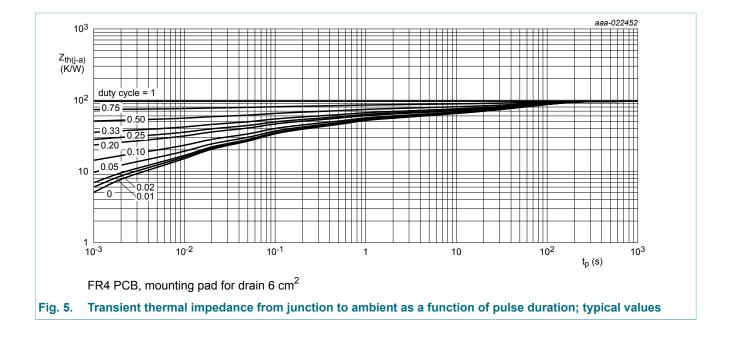




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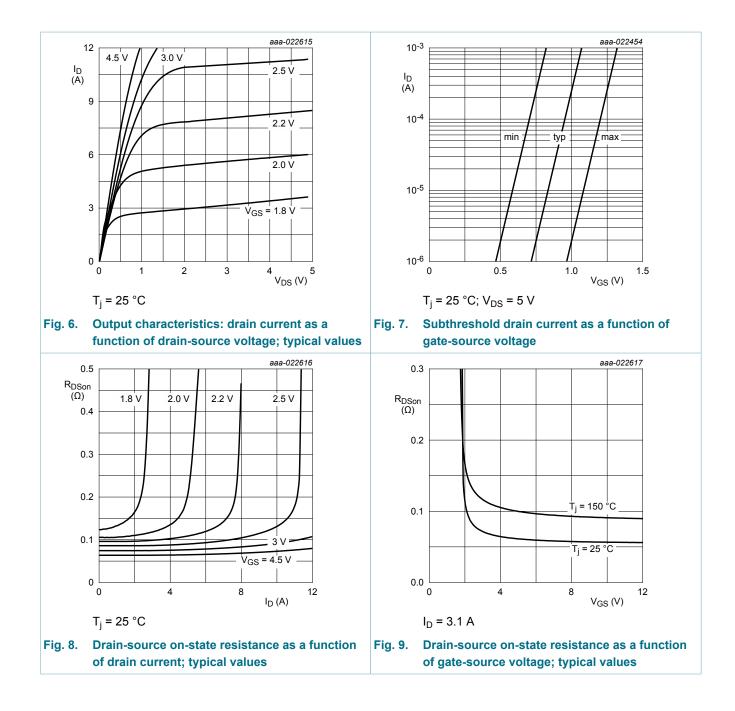
# **PMDPB56XNEA**

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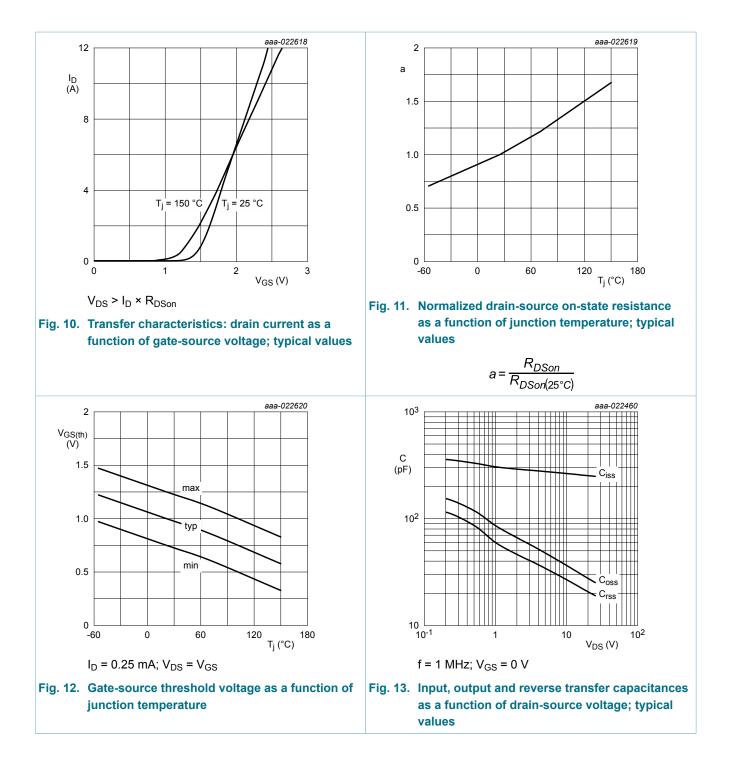
# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics (per transistor)	· · · · ·				
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	30	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = 250 μA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	0.75	1	1.25	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 30 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
I <sub>GSS</sub> gate	gate leakage current	$V_{GS}$ = 12 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		$V_{GS}$ = 4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	2	μA
		$V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-2	μA
R <sub>DSon</sub> drain-source resistance	drain-source on-state	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 3.1 A; T <sub>j</sub> = 25 °C	-	55	72	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3.1 A; T <sub>j</sub> = 150 °C	-	92	121	mΩ
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 2.6 A; T <sub>j</sub> = 25 °C	-	72	102	mΩ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 3.1 A; T <sub>j</sub> = 25 °C	-	12	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	-	9.2	-	Ω
Dynamic ch	aracteristics (per transist	or)			1	
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 15 V; I <sub>D</sub> = 3.1 A; V <sub>GS</sub> = 4.5 V;	-	2.9	5	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.4	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.8	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	256	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	31	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	23	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; I <sub>D</sub> = 8 A; V <sub>GS</sub> = 4.5 V;	-	9	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C	-	20	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	19	-	ns
t <sub>f</sub>	fall time		-	7	-	ns
Source-drai	n diode (per transistor)	· · ·	1			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1.1 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.7	1.2	V



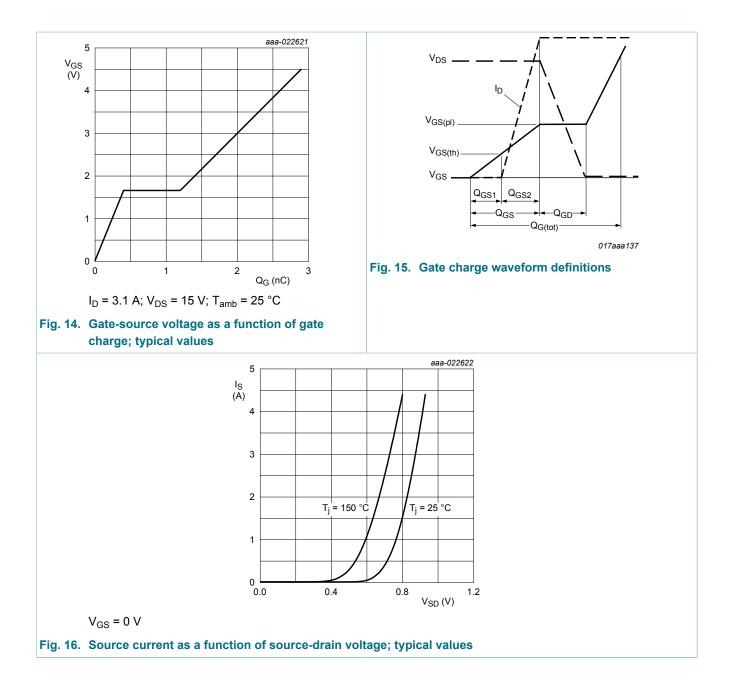
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## **PMDPB56XNEA**

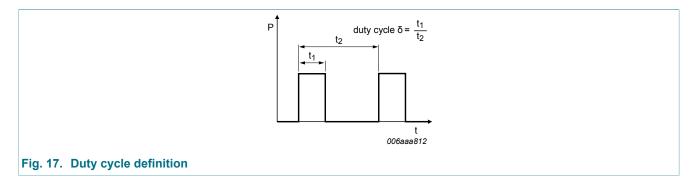


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# **PMDPB56XNEA**



### **11. Test information**

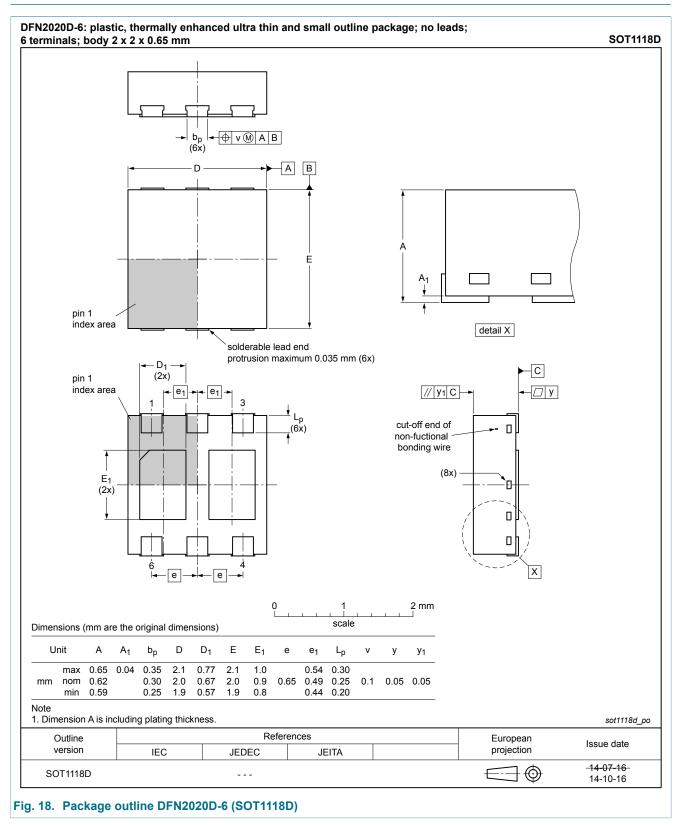


### **11.1 Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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### 12. Package outline

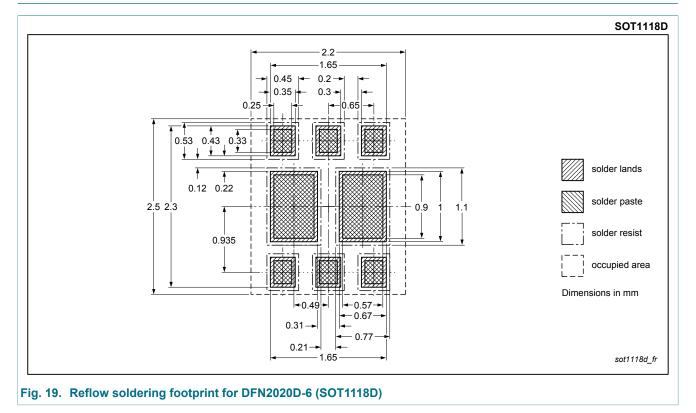


PMDPB56XNEA

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#### 30 V, dual N-channel Trench MOSFET

# 13. Soldering



# 14. Revision history

Table 8. Revision his	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMDPB56XNEA v.1	20160419	Product data sheet	-	-

#### 30 V, dual N-channel Trench MOSFET

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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